

# **ABSTRACT OF THE DISCLOSURE**

Method for detecting whether the alignment of bit  
line contacts and active areas in DRAM devices is normal,  
and a test device thereof. In the present invention a  
5 plurality of memory cells are formed in the memory area  
and at least one test device is formed in the scribe line  
region simultaneously. A first resistance and a second  
resistance are detected by the test device. Normal  
alignment of the bit line and the bar-type active area of  
10 the test device is determined according to the first  
resistance and the second resistance. Finally, whether  
the alignment of the bit line contacts and the active  
areas in memory areas is normal is determined according  
to whether the alignment of the bit line contact and bar-  
15 type active area of the test device is normal.